

NTP75N06, NTB75N06

Power MOSFET 75 Amps, 60 Volts N-Channel TO-220 and D²PAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	60	Vdc
Drain-to-Gate Voltage (R _{GS} = 10 MΩ) Gate-to-Source Voltage	V _{DGR}	60	Vdc

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 1) (V _{GS} = 0 Vdc, I _D = 250 μAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	60 -	71 73	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc, T _J = 150°C)	I _{DSS}	- -	- -	10 100	μAdc
Gate-Body Leakage Current (V _{GS} = ±20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	±100	nAdc

ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage (Note 1) (V _{DS} = V _{GS} , I _D = 250 μAdc) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	2.0 -	2.8 8.0	4.0 -	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 1) (V _{GS} = 10 Vdc, I _D = 37.5 Adc)	R _{DS(on)}	-	8.2	9.5	mOhm
Static Drain-to-Source On-Voltage (Note 1) (V _{GS} = 10 Vdc, I _D = 75 Adc) (V _{GS} = 10 Vdc, I _D = 37.5 Adc, T _J = 150°C)	V _{DS(on)}	- -	0.72 0.63	0.86 -	Vdc
Forward Transconductance (Note 1) (V _{DS} = 15 Vdc, I _D = 37.5 Adc)	g _{FS}	-	40.2	-	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	3220	4510	pF
Output Capacitance		C _{oss}	-	1020	1430	
Transfer Capacitance		C _{rss}	-	234	330	

SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	(V _{DD} = 30 Vdc, I _D = 75 Adc, V _{GS} = 10 Vdc, R _G = 9.1 Ω) (Note 1)	t _{d(on)}	-	16	25	ns
Rise Time		t _r	-	112	155	
Turn-Off Delay Time		t _{d(off)}	-	90	125	
Fall Time		t _f	-	100	140	
Gate Charge	(V _{DS} = 48 Vdc, I _D = 75 Adc, V _{GS} = 10 Vdc) (Note 1)	Q _T	-	92	130	nC
		Q ₁	-	14	-	
		Q ₂	-	44	-	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	(I _S = 75 Adc, V _{GS} = 0 Vdc) (Note 1) (I _S = 75 Adc, V _{GS} = 0 Vdc, T _J = 150°C)	V _{SD}	- -	1.0 0.9	1.1 -	Vdc
Reverse Recovery Time	(I _S = 75 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs) (Note 1)	t _{rr}	-	77	-	ns
		t _a	-	49	-	
		t _b	-	28	-	
Reverse Recovery Stored Charge		Q _{RR}	-	0.16	-	μC

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperatures.

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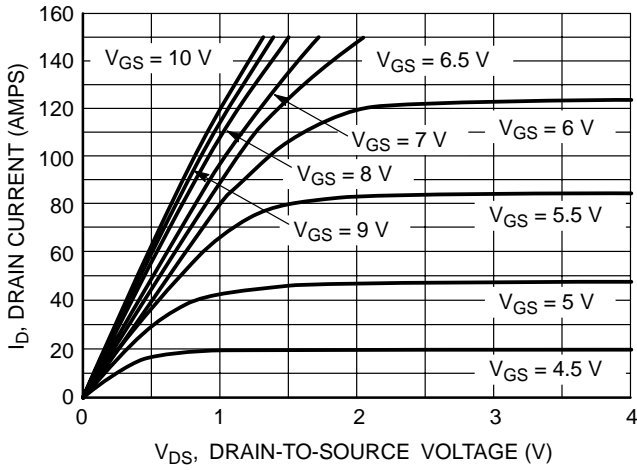


Figure 1. On-Region Characteristics

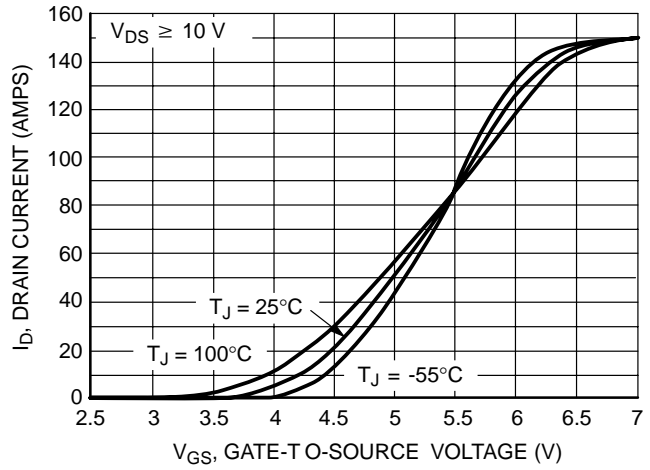


Figure 2. Transfer Characteristics

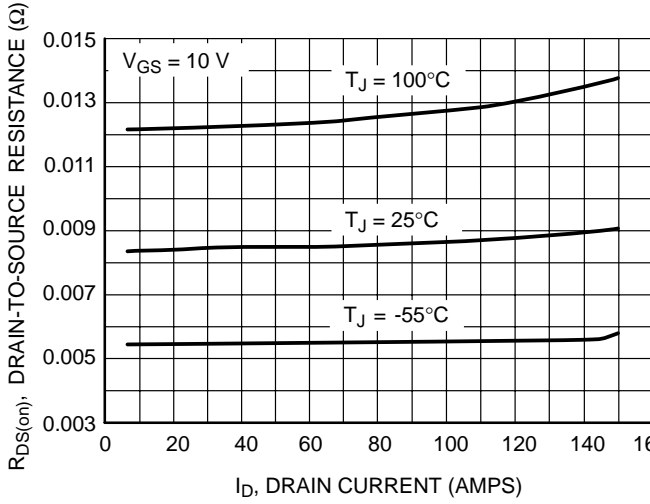


Figure 3. On-Resistance vs. Gate-to-Source Voltage

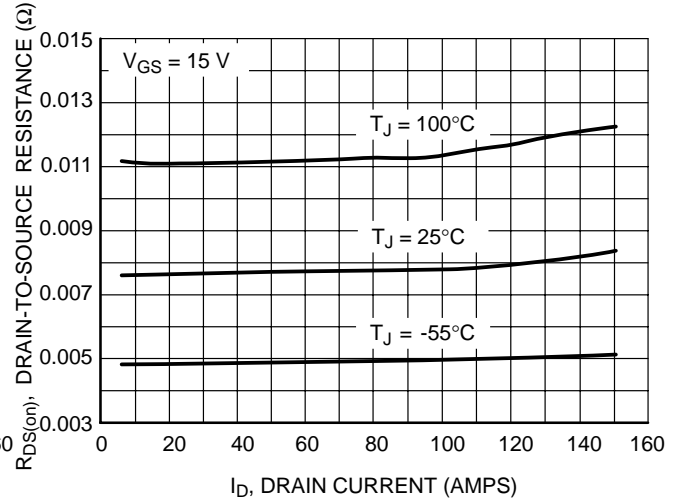


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

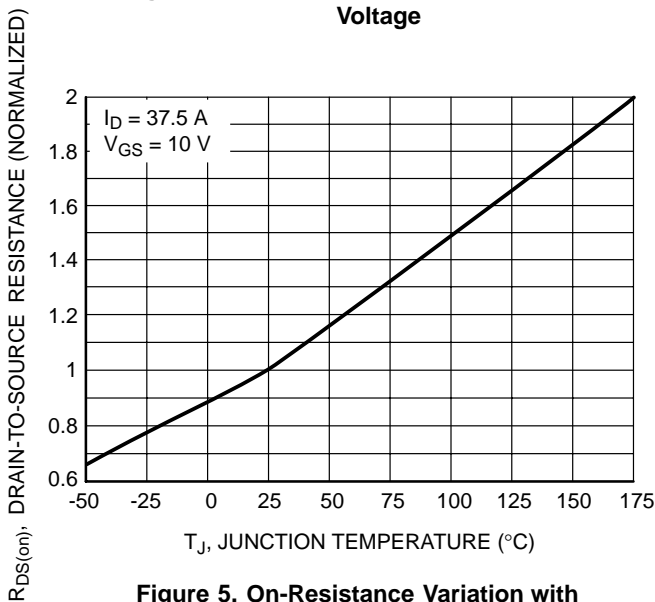


Figure 5. On-Resistance Variation with Temperature

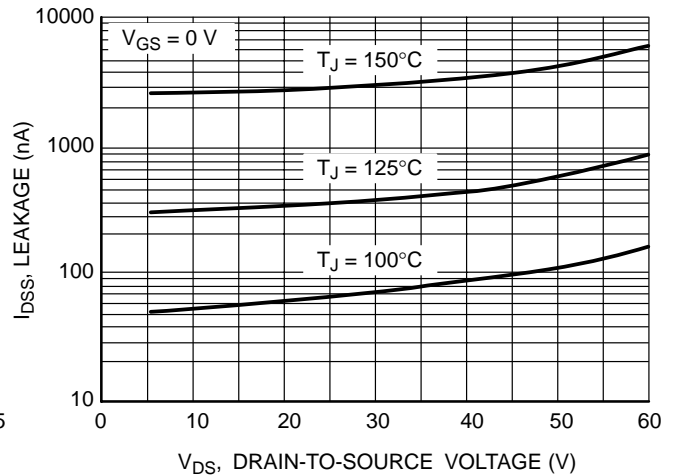


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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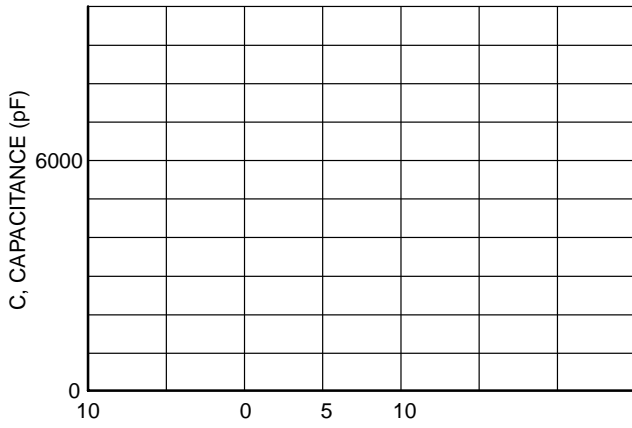


Figure 7. Capacitance Variation

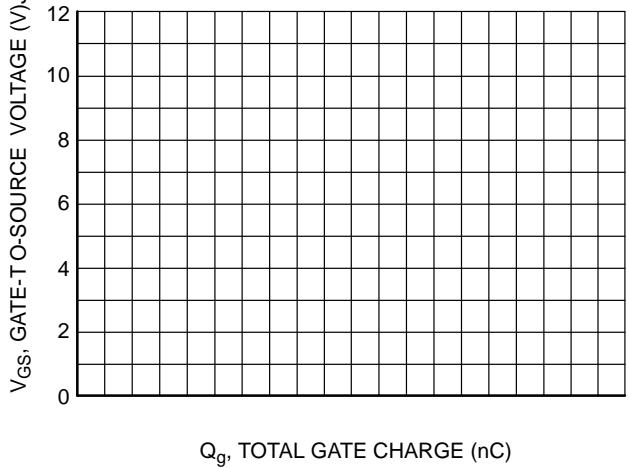
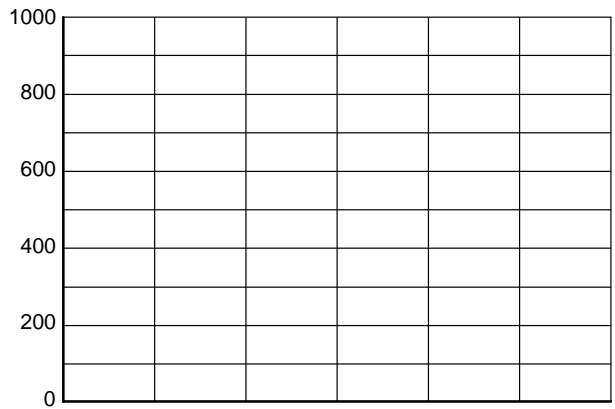
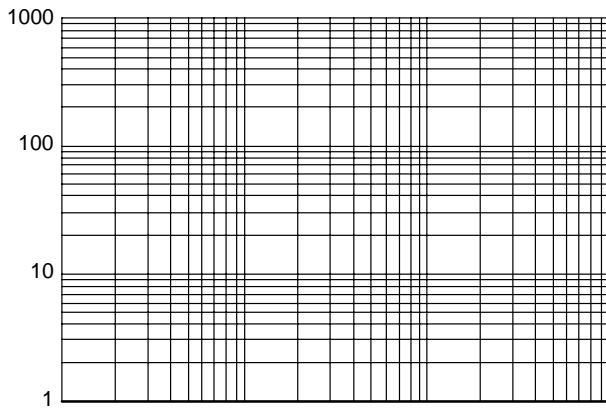
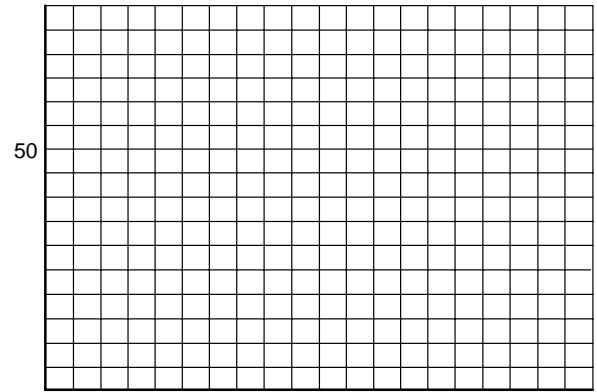
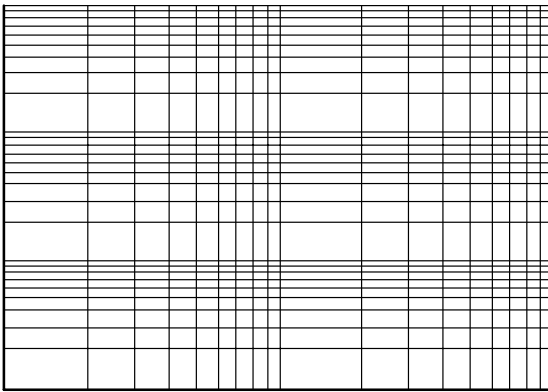


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge



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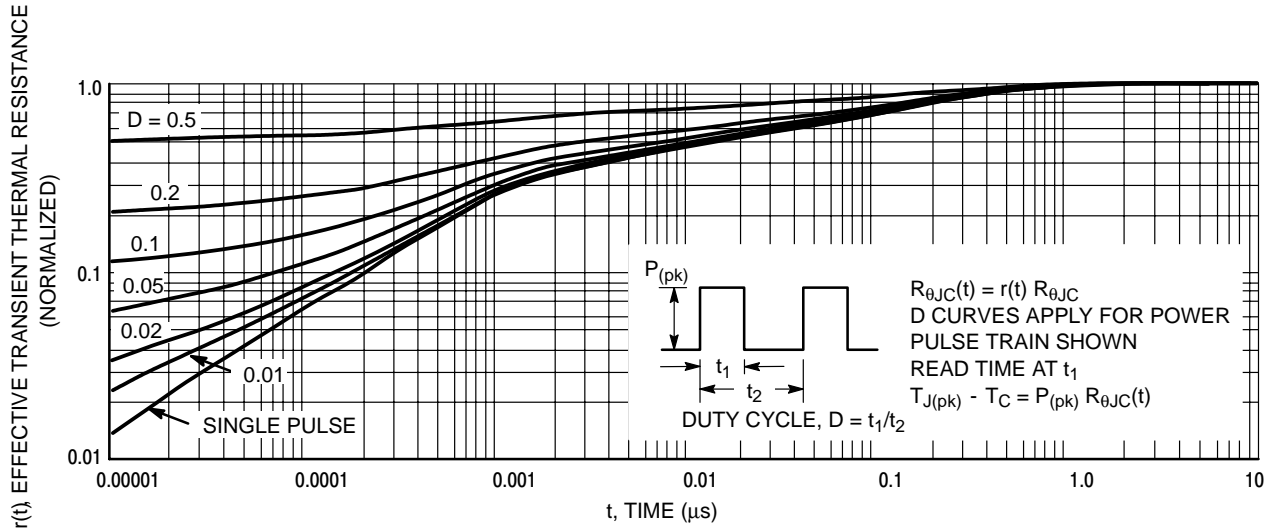
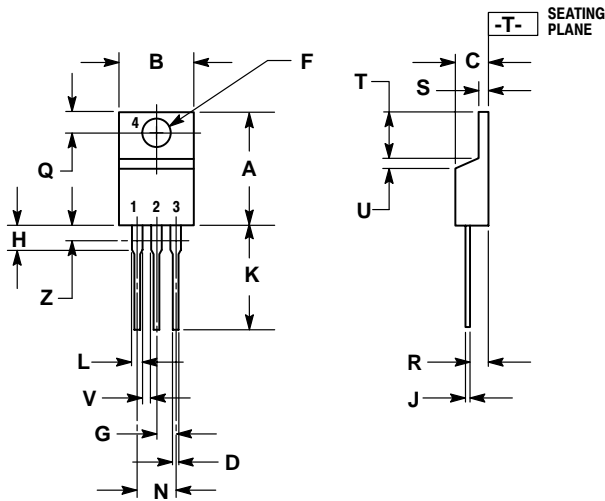


Figure 13. Thermal Response

PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

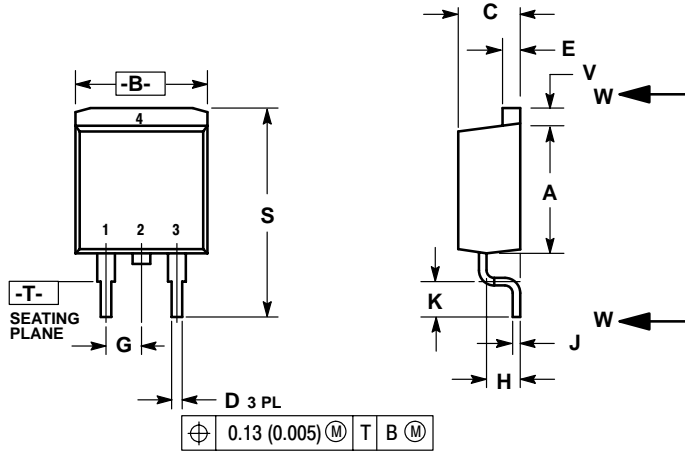
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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PACKAGE DIMENSIONS

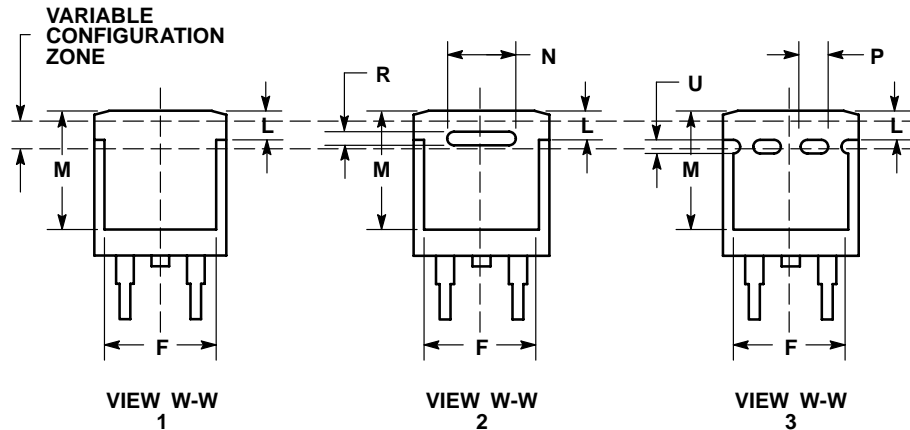
D²PAK
CASE 418B-04
ISSUE H



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN



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